

NCE N-Channel Super Trench Power MOSFET

Description

The NCEP02505S uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{\text{DS(ON)}}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

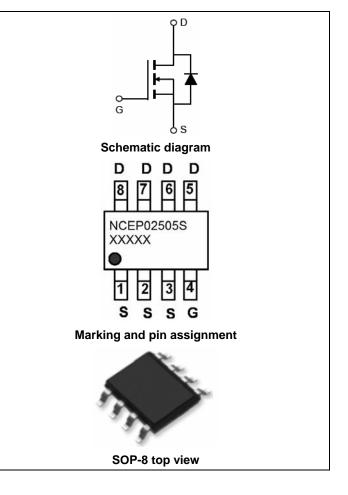
General Features

- V_{DS} =250V, I_D =5A $R_{DS(ON)}$ =60m Ω (typical) @ V_{GS} =10V
- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- 150 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

Application

- LED backlighting
- Ideal for high-frequency switching and synchronous rectification

100% UIS TESTED!



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP02505S	NCEP02505S	SOP-8	Ø330mm	12mm	4000 units

Absolute Maximum Ratings (T_A=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	250	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	I _D	5	Α
Drain Current-Continuous(T _C =100°C)	I _D (100℃)	3.5	Α
Pulsed Drain Current	I _{DM}	20	А
Maximum Power Dissipation	P _D	3.5	W
Single pulse avalanche energy (Note 5)	E _{AS}	320	mJ
Operating Junction and Storage Temperature Range	T_{J} , T_{STG}	-55 To 150	$^{\circ}$ C

Thermal Characteristic

Thermal Résistance, Junction-to-Ambient ^(Note 2)	R _{θJA}	35.7	°C/W
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Electrical Characteristics (T_A =25 $^{\circ}$ C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	·					
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	250	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =250V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V_{GS} =±20V, V_{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)	<u> </u>					
Gate Threshold Voltage	$V_{GS(th)}$	V _{DS} =V _{GS} ,I _D =250μA	2.5	3.5	4.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V_{GS} =10V, I_D =5A	-	60	70	mΩ
Forward Transconductance	g FS	V_{DS} =5 V , I_{D} =5 A	15	-	-	S
Dynamic Characteristics (Note4)			•			
Input Capacitance	C _{lss}	\/ 405\/\/ 0\/	-	1600		PF
Output Capacitance	C _{oss}	V _{DS} =125V,V _{GS} =0V,	-	92		PF
Reverse Transfer Capacitance	C _{rss}	r-1.0ivinz	-	4.3		PF
Switching Characteristics (Note 4)			•			
Turn-on Delay Time	t _{d(on)}		-	7	-	nS
Turn-on Rise Time	t _r	V _{DD} =125V, R _L =25Ω	-	9	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{G} =3 Ω	-	25	-	nS
Turn-Off Fall Time	t _f	F=1.0MHz V _{DD} =125V, R _L =25Ω	-	5	-	nS
Total Gate Charge	Qg	\/ -405\/ -54	-	24	-	nC
Gate-Source Charge	Q _{gs}	$V_{DS}=125V,I_{D}=5A,$ $V_{GS}=10V$	-	9.5	-	nC
Gate-Drain Charge	Q_{gd}	V _{GS} =10V	-	5.6	-	nC
Drain-Source Diode Characteristics				•		
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =5A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	5	Α
Reverse Recovery Time	t _{rr}	$T_J = 25^{\circ}C, I_F = I_S$	-	45	-	nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	-	160	-	nC

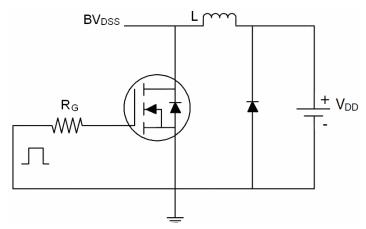
Notes:

- ${\it 1. Repetitive Rating: Pulse width limited by maximum junction temperature.}\\$
- 2. Surface Mounted on FR4 Board, $t \le 10$ sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25 $^{\circ}\!\!\mathrm{C}$,V_DD=50V,V_G=10V,L=0.5mH,Rg=25 Ω

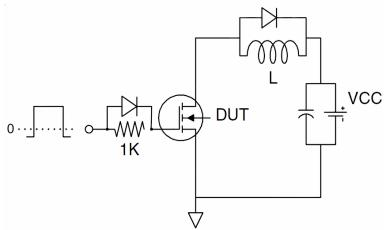


Test Circuit

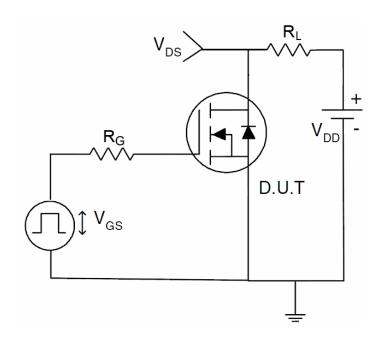
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit





Typical Electrical and Thermal Characteristics

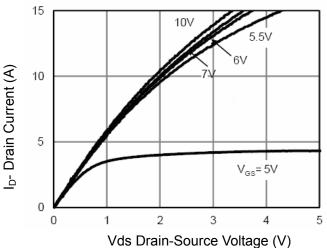


Figure 1 Output Characteristics

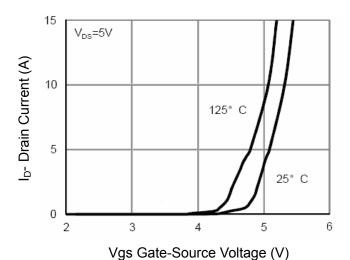


Figure 2 Transfer Characteristics

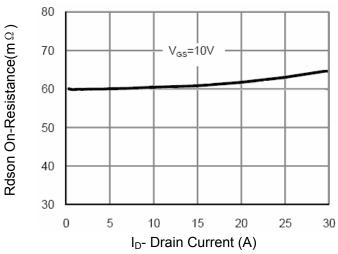


Figure 3 Rdson- Drain Current

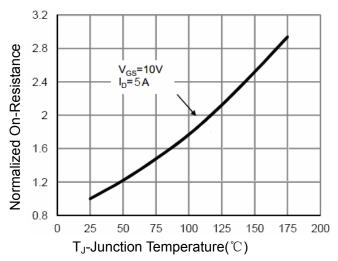


Figure 4 Rdson-Junction Temperature

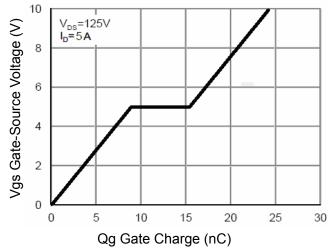


Figure 5 Gate Charge

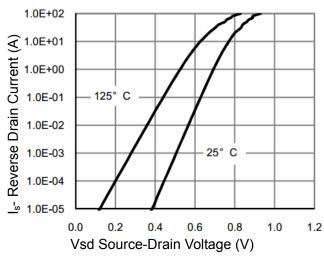


Figure 6 Source- Drain Diode Forward



l_D- Drain Current (A)

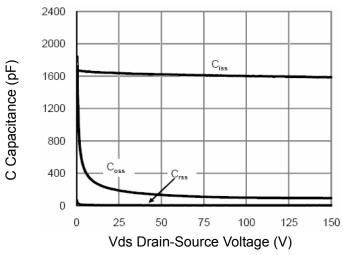


Figure 7 Capacitance vs Vds

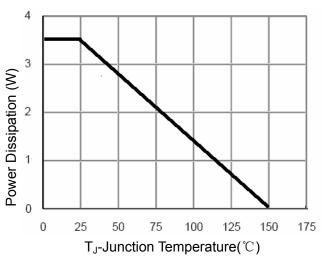


Figure 9 Power De-rating

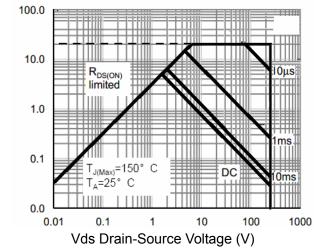


Figure 8 Safe Operation Area

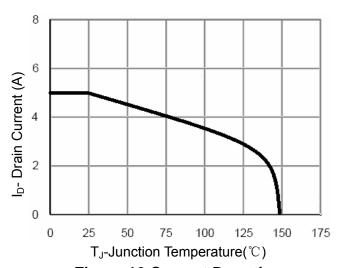


Figure 10 Current De-rating

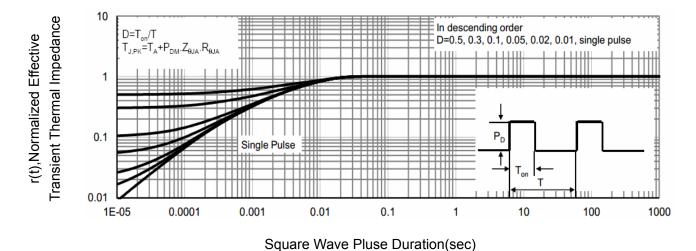
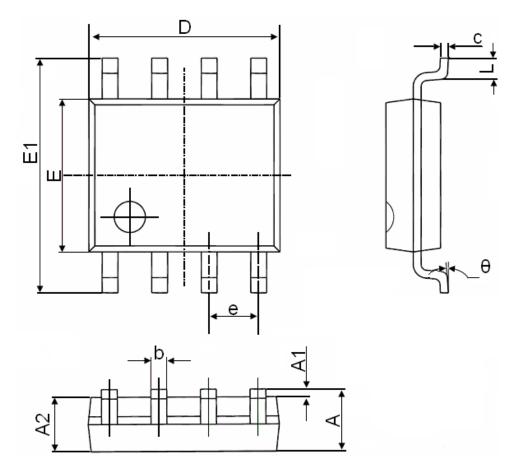


Figure 11 Normalized Maximum Transient Thermal Impedance



SOP-8 Package Information



Cumah al	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
Α	1.350	1.750	0.053	0.069	
A1	0.100	0.250	0.004	0.010	
A2	1.350	1.550	0.053	0.061	
b	0.330	0.510	0.013	0.020	
С	0.170	0.250	0.006	0.010	
D	4.700	5.100	0.185	0.200	
Е	3.800	4.000	0.150	0.157	
E1	5.800	6.200	0.228	0.244	
е	1.270	(BSC)	0.050	(BSC)	
L	0.400	1.270	0.016	0.050	
θ	0°	8°	0°	8°	

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NCEP02505S

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